

FQB22P10 / FQI22P10

P-Channel QFET MOSFET

-100 V, -22 A, 125 mΩ

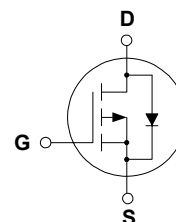
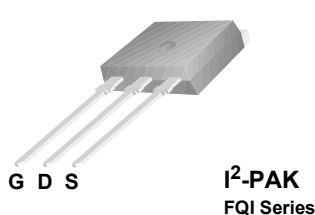
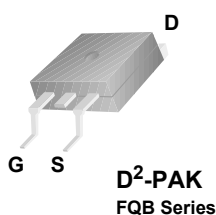


Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -22 A, -100 V, $R_{DS(on)} = 125 \text{ m}\Omega$ (Max) @ $V_{GS} = -10 \text{ V}$, $I_D = -11 \text{ A}$
- Low Gate Charge (Typ. 40 nC)
- Low Crss (Typ. 160 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FQB22P10 / FQI22P10	Unit
V _{DSS}	Drain-Source Voltage	-100	V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	-22	A
		-15.6	A
I _{DM}	Drain Current - Pulsed (Note 1)	-88	A
V _{GSS}	Gate-Source Voltage	±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	710	mJ
I _{AR}	Avalanche Current (Note 1)	-22	A
E _{AR}	Repetitive Avalanche Energy (Note 1)	12.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	-6.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *	3.75	W
	Power Dissipation (T _C = 25°C) - Derate above 25°C	125	W
		0.83	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	--	1.2	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient *	--	40	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-100	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$, Referenced to 25°C	--	-0.1	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	μA
		$V_{DS} = -80\text{ V}, T_C = 125^\circ\text{C}$	--	--	-10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-2.0	--	-4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -11\text{ A}$	--	0.096	0.125	Ω
g_{FS}	Forward Transconductance	$V_{DS} = -40\text{ V}, I_D = -11\text{ A}$ (Note 4)	--	13.5	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	1170	1500	pF
C_{oss}	Output Capacitance		--	460	600	pF
C_{riss}	Reverse Transfer Capacitance		--	160	200	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -50\text{ V}, I_D = -22\text{ A},$ $R_G = 25\ \Omega$	--	17	45	ns	
t_r	Turn-On Rise Time		--	170	350	ns	
$t_{d(off)}$	Turn-Off Delay Time		(Note 4, 5)	--	60	130	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	110	230	ns
Q_g	Total Gate Charge	$V_{DS} = -80\text{ V}, I_D = -22\text{ A},$ $V_{GS} = -10\text{ V}$	--	40	50	nC	
Q_{gs}	Gate-Source Charge		(Note 4, 5)	--	7.0	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	21	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	-22	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-88	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -22\text{ A}$	--	--	-4.0	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = -22\text{ A},$	--	110	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	0.6	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 2.2\text{mH}, I_{AS} = -22\text{A}, V_{DD} = -25\text{V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq -22\text{A}, di/dt \leq 300\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

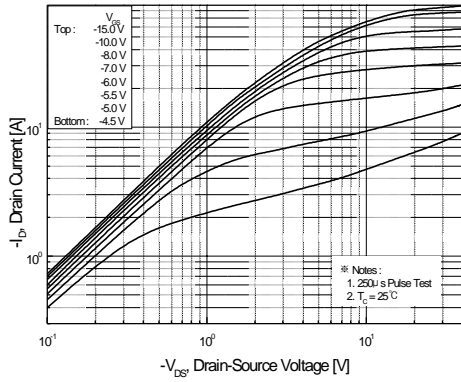


Figure 1. On-Region Characteristics

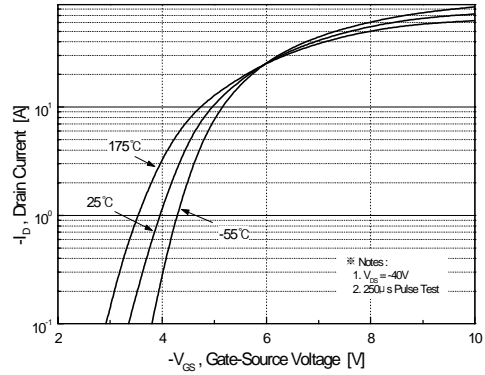


Figure 2. Transfer Characteristics

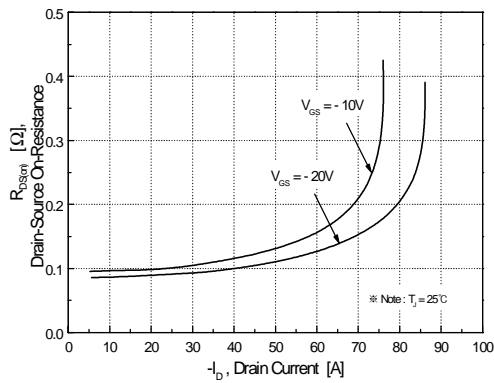


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

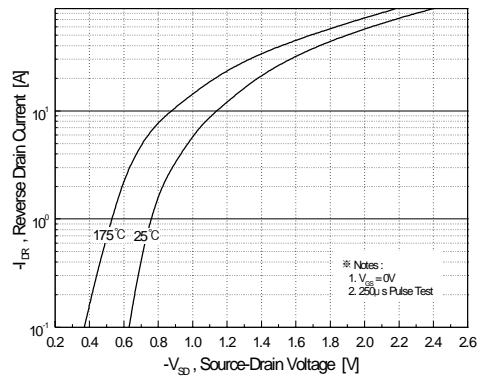


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

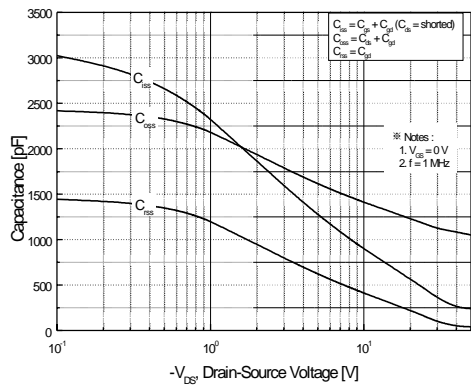


Figure 5. Capacitance Characteristics

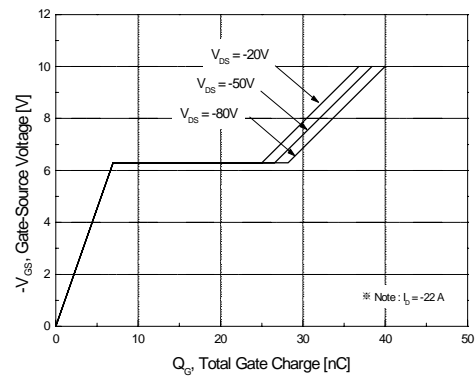


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

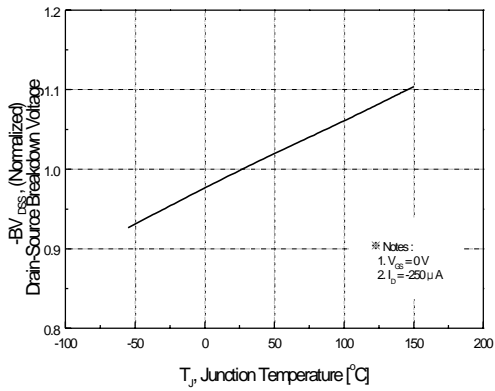


Figure 7. Breakdown Voltage Variation vs. Temperature

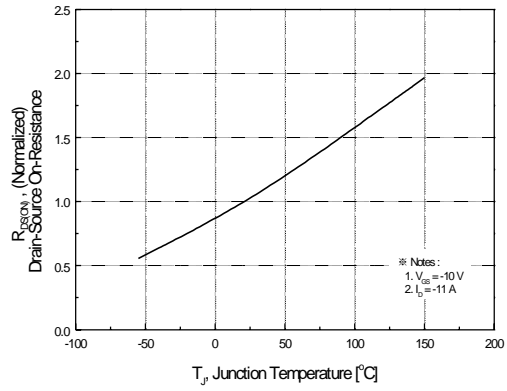


Figure 8. On-Resistance Variation vs. Temperature

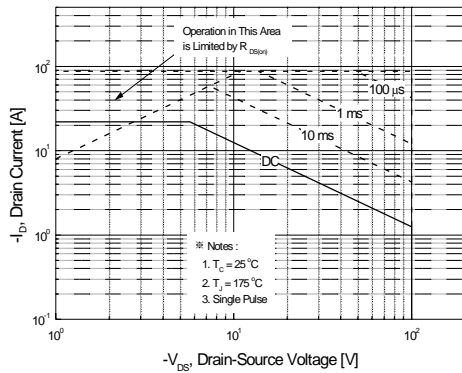


Figure 9. Maximum Safe Operating Area

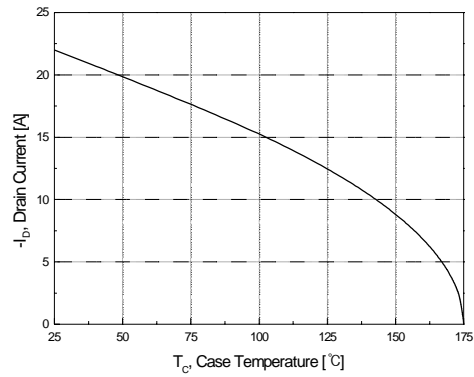


Figure 10. Maximum Drain Current vs. Case Temperature

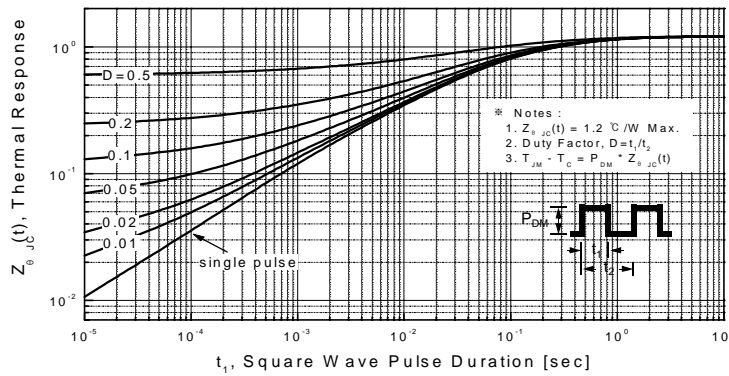
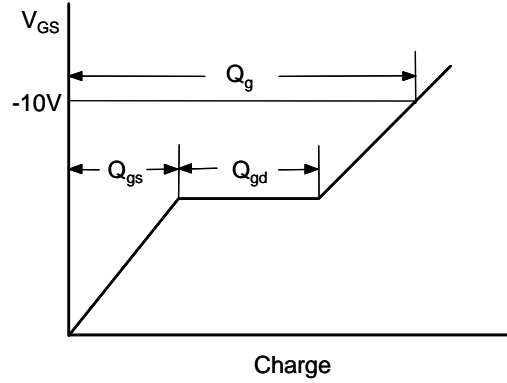
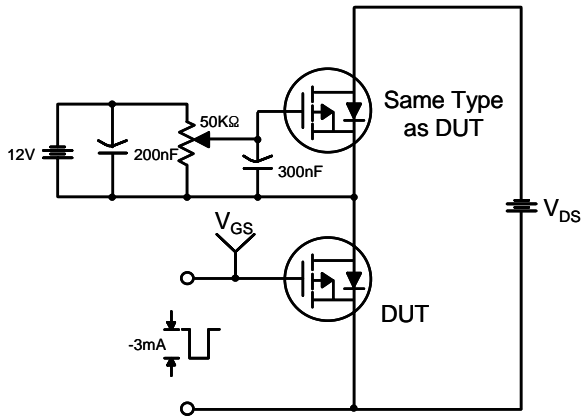
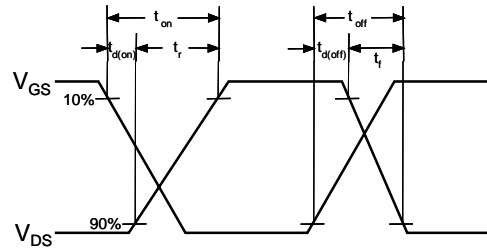
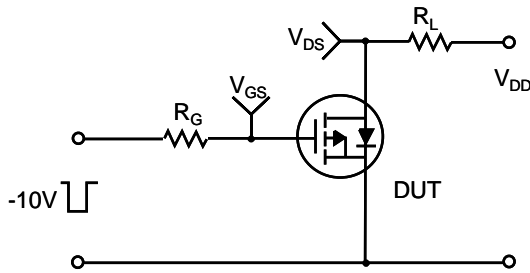


Figure 11. Transient Thermal Response Curve

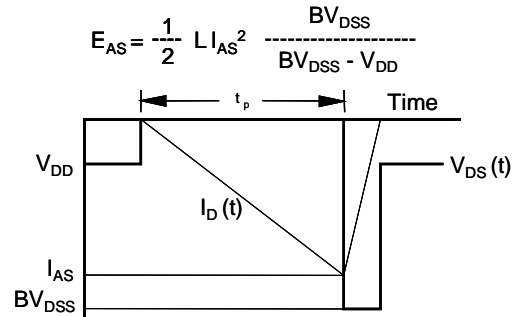
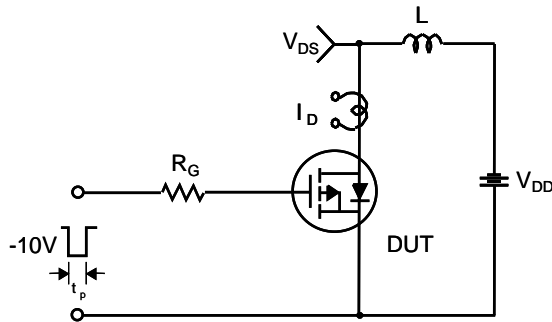
Gate Charge Test Circuit & Waveform



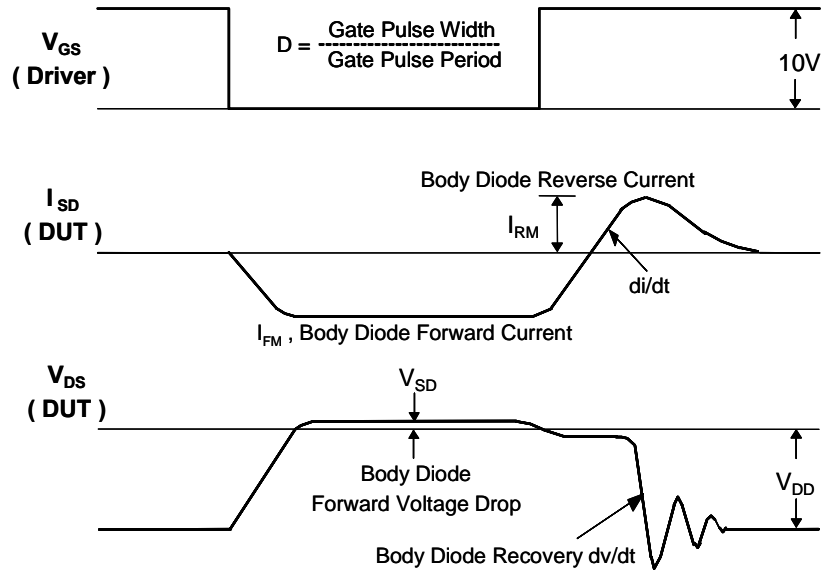
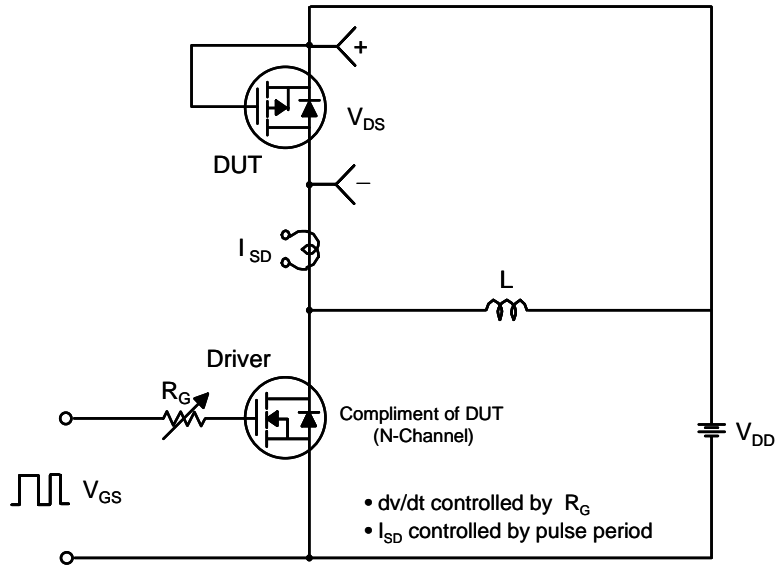
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

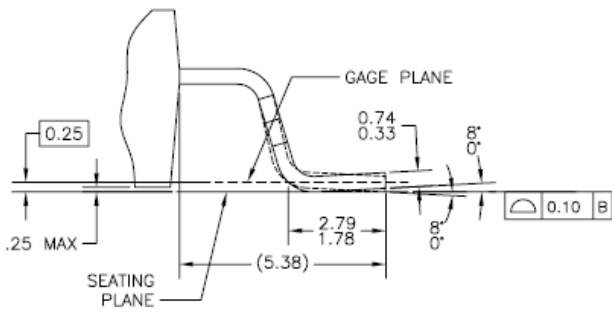
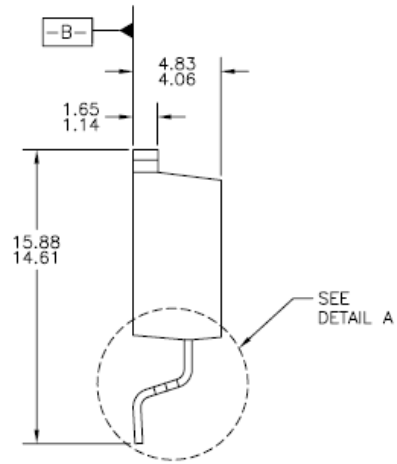
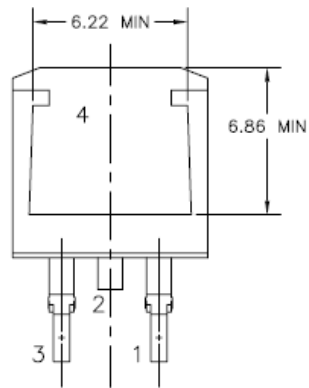
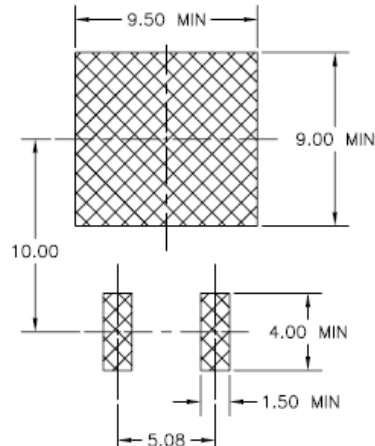
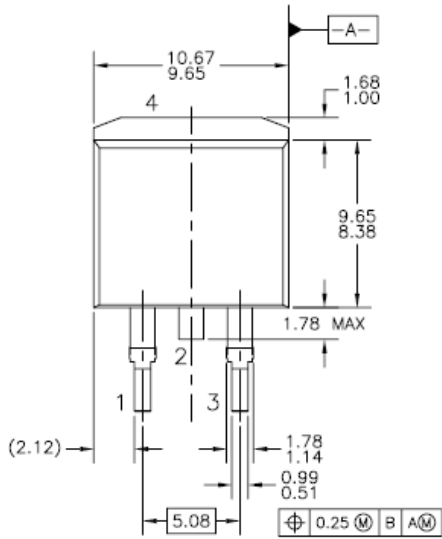


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

D² - PAK

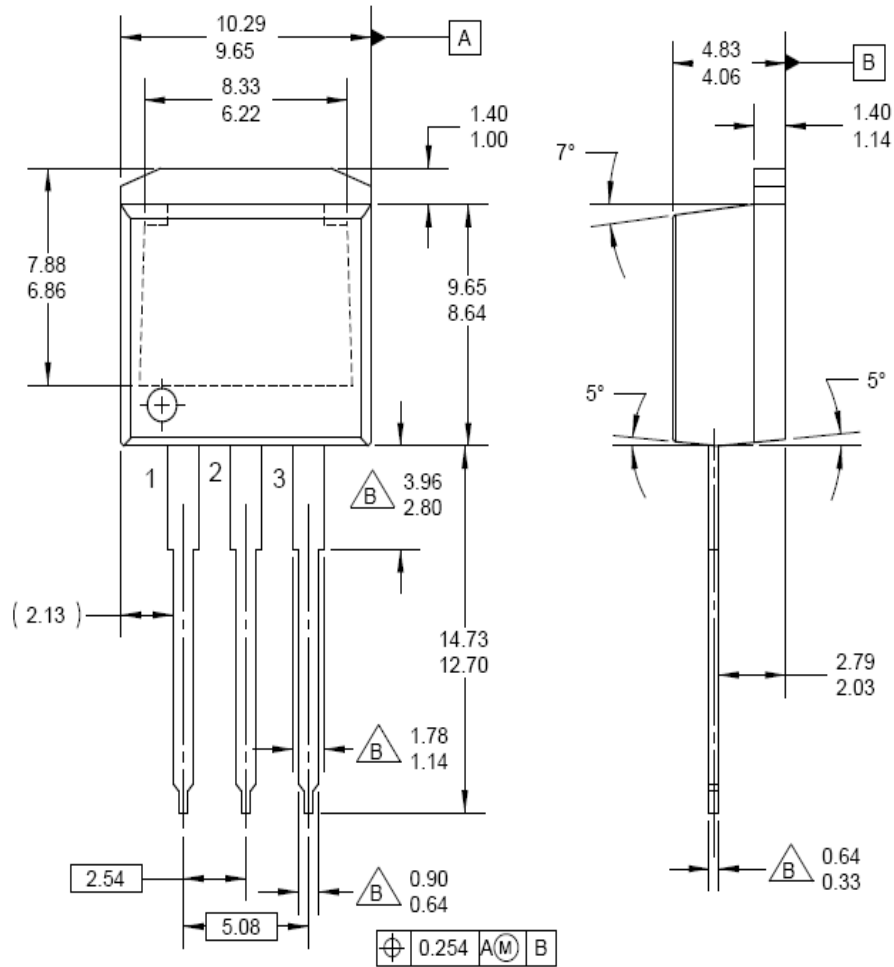


DETAIL A, ROTATED 90°
SCALE: 10X

Dimensions in Millimeters

Package Dimensions (Continued)

I² - PAK



FQB22P10 / FQI22P10 P-Channel MOSEFT

Dimensions in Millimeters



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